L Number	Hits	Search Text	DB	Time stamp
-	12	' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	USPAT	2003/09/16 09:12
		or ("6395590") or ("6372564") or		
		("6346466") or ("6255166") or ("6583007") or ("6566203") or ("6555427") or		
		("6518125") or ("6482708")).PN.		
_	2		USPAT;	2003/09/02 14:33
		(nitride adj (read-only) adj memory)) and	US-PGPUB;	
		(ono same (wet adj etching) same (dop\$6 or	EPO; JPO;	
		implant\$6) same (buried adj bit adj line))	DERWENT; IBM TDB	
_	2	(ono same (wet adj etching) same (dop\$6 or	USPAT;	2003/09/02 14:12
	_	<pre>implant\$6) same (buried adj bit adj line))</pre>	US-PGPUB;	
	1	and ((nitride adj read adj only adj	EPO; JPO;	
		memory) or (nitride adj (read-only) adj	DERWENT;	
	3	<pre>memory)) ((nitride adj read adj only adj memory) or</pre>	IBM_TDB USPAT;	2003/09/02 14:15
-]	(nitride adj (read-only) adj memory)) and	US-PGPUB;	2003/03/02 14.13
		ono and (wet adj etching) and (dop\$6 or	EPO; JPO;	
		implant\$6) and (buried adj bit adj line)	DERWENT;	
			IBM_TDB	0000 (00 (00 14 07
-	8	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory)) and	USPAT; US-PGPUB;	2003/09/02 14:27
		ono and (wet adj etching) and (dop\$6 or	EPO; JPO;	
		implant\$6) and (bit adj line)	DERWENT;	
			IBM_TDB	
-	94	((nitride adj read adj only adj memory) or	USPAT;	2003/09/02 14:33
		(nitride adj (read-only) adj memory)) and ono and (dop\$6 or implant\$6)	US-PGPUB; EPO; JPO;	
		ono and (doppe of implantation)	DERWENT;	
			IBM_TDB	
-	94	((t +	USPAT;	2003/09/02 14:34
		or (nitride adj (read-only) adj memory))	US-PGPUB;	
		and ono and (dop\$6 or implant\$6)) and @ad<=20021115	EPO; JPO; DERWENT;	
			IBM TDB	
-	81	((((nitride adj read adj only adj memory)	USPAT;	2003/09/02 14:29
		or (nitride adj (read-only) adj memory))	US-PGPUB; EPO; JPO;	
		and ono and (dop\$6 or implant\$6)) and @ad<=20021115) and bit	DERWENT;	
	*		IBM TDB	
-	72	((((nitride adj read adj only adj memory)	USPAT;	2003/09/02 14:34
		or (nitride adj (read-only) adj memory))	US-PGPUB; EPO; JPO;	
		and ono and (dop\$6 or implant\$6)) and @ad<=20021115) and (bit adj line)	DERWENT;	
		caa zooziiio, ana (oit aaj iine,	IBM TDB	
-	2	((nitride adj read adj only adj memory) or	USPAT;	2003/09/02 14:33
		(nitride adj (read-only) adj memory) or	US-PGPUB;	
		nrom) and (ono same (wet adj etching) same (dop\$6 or implant\$6) same (buried adj bit	EPO; JPO; DERWENT;	
		adj line))	IBM TDB	
-	157	((nitride adj read adj only adj memory) or	USPĀT;	2003/09/02 14:33
		(nitride adj (read-only) adj memory) or	US-PGPUB;	
		NROM) and ono and (dop\$6 or implant\$6)	EPO; JPO; DERWENT;	
			IBM TDB	
-	150	(((nitride adj read adj only adj memory)	USPAT;	2003/09/02 14:34
		or (nitride adj (read-only) adj memory) or	US-PGPUB;	
		NROM) and ono and (dop\$6 or implant\$6)) and @ad<=20021115	EPO; JPO; DERWENT;	
		and ead\-20021113	IBM TDB	
-	115	((((nitride adj read adj only adj memory)	USPAT;	2003/09/02 14:46
		or (nitride adj (read-only) adj memory) or	US-PGPUB;	
		NROM) and ono and (dop\$6 or implant\$6))	EPO; JPO;	
		and @ad<=20021115) and (bit adj line)	DERWENT; IBM TDB	
-	85	(((((nitride adj read adj only adj memory)	USPAT;	2003/09/02 14:49
		or (nitride adj (read-only) adj memory) or	US-PGPUB;	
		NROM) and one and (dop\$6 or implant\$6))	EPO; JPO;	·
		and @ad<=20021115) and (bit adj line)) and (etch\$5)	DERWENT;	
	l .	(6000140)	1701 100	l

-	24	(((((nitride adj read adj only adj memory)	USPAT;	2003/09/02 14:48
		or (nitride adj (read-only) adj memory) or	US-PGPUB;	
		NROM) and one and (dop\$6 or implant\$6))	EPO; JPO;	
		and @ad<=20021115) and (bit adj line)) and	DERWENT; IBM TDB	
	30	(wet adj etch\$5)	USPAT;	2003/09/02 14:47
-	30		l	2003/09/02 14:47
		or (nitride adj (read-only) adj memory) or	US-PGPUB;	
		NROM) and one and (dop\$6 or implant\$6))	EPO; JPO; DERWENT;	
		and @ad<=20021115) and (bur\$4 adj bit adj line)	IBM TDB	
	6	· ·	USPAT;	2003/09/02 14:47
_	8	memory) or (nitride adj (read-only) adj	US-PGPUB;	2003/03/02 14.47
		memory) or NROM) and ono and (dop\$6 or	EPO; JPO;	
		implant\$6)) and @ad<=20021115) and (bit	DERWENT;	
		adj line)) and (wet adj etch\$5)) and	IBM TDB	
		(bur\$4 adj bit adj line)	_	
_	6	(((((nitride adj read adj only adj memory)	USPAT;	2003/09/02 14:49
1	ļ	or (nitride adj (read-only) adj memory) or	US-PGPUB;	
		NROM) and ono and (dop\$6 or implant\$6))	EPO; JPO;	
		and @ad<=20021115) and (bur\$4 adj bit adj	DERWENT;	
i		line)) and (wet adj etch\$5)	IBM_TDB	
_	26	(((((nitride adj read adj only adj memory)	USPĀT;	2003/09/03 07:57
		or (nitride adj (read-only) adj memory) or	US-PGPUB;	
		NROM) and ono and (dop\$6 or implant\$6))	EPO; JPO;	
		and @ad<=20021115) and (bur\$4 adj bit adj	DERWENT;	
		line)) and (etch\$5)	IBM_TDB	
-	99		USPAT;	2003/09/03 10:52
		(nitride adj (read-only) adj memory) or	US-PGPUB;	
		(NROM)) and ((ono or (oxide adj nitride	EPO; JPO;	
		adj oxide) or ((silicon adj oxide) adj	DERWENT;	
<u> </u>		(silicon adj nitride) adj (silicon adj	IBM_TDB	
		oxide))) and (dop\$6 or implant\$6) and		
		@ad<=20021115) and (bit adj line) and		
	1	(word adj line)	USPAT	2003/09/03 12:50
-	$\begin{bmatrix} 1 \\ 1 \end{bmatrix}$	("6566203").PN. ("6461906").PN.	USPAT	2003/09/03 12:30
-	1	("5496753").PN.	USPAT	2003/09/03 13:07
	329	(438/261).CCLS.	USPAT;	2003/09/03 13:07
-	329	(430/201).0005.	US-PGPUB;	2003, 03, 03 13.0.
			EPO; JPO;	
			DERWENT;	·
			IBM TDB	
-	1390	(438/257).CCLS.	USPAT;	2003/09/03 13:09
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	Ī		IBM_TDB	
-	578	(438/258).CCLS.	USPAT;	2003/09/03 13:08
	l		US-PGPUB;	
	1		EPO; JPO;	
	ļ		DERWENT;	
	1	(420/250)	IBM_TDB	2002/00/02 12:00
-	330	(438/259).CCLS.	USPAT;	2003/09/03 13:08
	[US-PGPUB; EPO; JPO;	
	1		DERWENT;	
	Ī		IBM TDB	
l _	98	(438/260).CCLS.	USPAT;	2003/09/03 13:08
		(430/200).0000.	US-PGPUB;	-555, 55, 55 15.00
	[EPO; JPO;	
	[DERWENT;	
	1		IBM TDB	
_	329	(438/261).CCLS.	USPAT;	2003/09/03 13:08
		,	US-PGPUB;	
	Ī		EPO; JPO;	
1	[DERWENT;	
	1		IBM_TDB	
-	199	(438/262).CCLS.	USPAT;	2003/09/03 13:08
			US-PGPUB;	
	[EPO; JPO;	
	[DERWENT;	
	<u></u>		IBM TDB	<u> </u>

_	711	(438/526).CCLS.	USPAT;	2003/09/03 13:09
-	/11	(436/326).CCLS.	US-PGPUB;	2003/03/03 13.03
			EPO; JPO;	
			DERWENT;	
		4400 (075)	IBM_TDB	2002/00/02 12:00
-	694	(438/275).CCLS.	USPAT; US-PGPUB;	2003/09/03 13:09
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	246	(438/294).CCLS.	USPAT;	2003/09/03 13:10
			US-PGPUB;	
			EPO; JPO; DERWENT;	
	1		IBM TDB	
_	152	(438/216).CCLS.	USPAT;	2003/09/03 13:10
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1_	333	(438/591).CCLS.	IBM_TDB USPAT;	2003/09/03 13:10
		(430/371).0083.	US-PGPUB;	2003/03/03 13.10
			EPO; JPO;	
			DERWENT;	
		(420 /016) 607.0	IBM_TDB	2002/00/02 12 12
_	152	(438/216).CCLS.	USPAT; US-PGPUB;	2003/09/03 13:10
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	613	(438/264).CCLS.	USPAT;	2003/09/03 13:11
	ļ		US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	636	(438/527).CCLS.	USPĀT;	2003/09/03 13:12
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	750	(438/287).CCLS.	USPĀT;	2003/09/03 13:12
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	74	(438/954).CCLS.	USPAT;	2003/09/03 13:12
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	20	 semiconductor same ono same (etch\$4 adj	USPAT;	2003/09/03 15:28
		stop)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	20	(semiconductor same ono same (etch\$4 adj	IBM_TDB USPAT;	2003/09/03 15:27
	1	stop)) and @ad<=20021115	US-PGPUB;	2003,03,03 13.27
		.,	EPO; JPO;	
			DERWENT;	
_	100	semigranductor and one and (atch add atch)	IBM_TDB USPAT;	2003/09/15 14:21
-	480	semiconductor and ono and (etch adj stop) and @ad<=20021115	USPAT; US-PGPUB;	2003/03/13 14:21
			EPO; JPO;	
1			DERWENT;	
		120/007 061 501	IBM_TDB	2002/00/15 14 27
-	12	438/287,261,591.ccls. and ono and (etch adj stop) and @ad<=20021115	USPAT; US-PGPUB;	2003/09/15 14:37
		44) 5000/ 4114 644-20021113	EPO; JPO;	
			DERWENT;	
			IBM TDB	

-	264	438/287,261,591.ccls. and ono and	USPAT;	2003/09/03 15:38
		@ad<=20021115	US-PGPUB;	
			EPO; JPO;	
	ł		DERWENT;	
			IBM TDB	
_	397	257/\$.ccls. and ono and (etch\$3 adj stop\$4	USPAT;	2003/09/15 14:52
		adj (layer or film)) and @ad<=20021115	US-PGPUB;	
		, 40, (20,00 01 ===, , =	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	340	438/\$.ccls. and ono and (etch\$3 adj stop\$4	USPAT;	2003/09/15 14:52
	540	adj (layer or film)) and @ad<=20021115	US-PGPUB;	=====================================
		adj (layer of lilm), and eday 20021113	EPO; JPO;	
			DERWENT;	
			IBM TDB	
		and (atabes add stared add (layer or	USPAT;	2003/09/15 14:53
-	502			2003/03/13 14:33
1		film)) and @ad<=20021115	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	2002/00/15 14:52
-	9	(ono same semiconductor same (etch\$3 adj	USPAT;	2003/09/15 14:53
		stop\$4 adj (layer or film))) and	US-PGPUB;	
		@ad<=20021115	EPO; JPO;	
			DERWENT;	
			IBM_TDB	_
-	478		USPAT;	2003/09/15 15:34
		stop\$4 adj (layer or film)) and	US-PGPUB;	
		@ad<=20021115	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	32968	liu.in.	USPĀT;	2003/09/15 15:36
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
_	10	liu.in. and cheng-jye	USPAT;	2003/09/15 15:35
]	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	[
l _	2054	hsiung.in.	USPAT;	2003/09/15 15:36
	2034	11024119.2111	US-PGPUB;	=====================================
	1		EPO; JPO;	1
	1		DERWENT;	
	1		IBM TDB	
_	66204	chen.in.	USPAT;	2003/09/15 15:36
	00294	CHGH. III.	US-PGPUB;	2003/03/13 13.30
	1		EPO; JPO;	
	1		DERWENT;	1
	· .			
	_	h-4 11	IBM_TDB	2002/00/15 15:27
-	3	hsiung.in. and tai-liang	USPAT;	2003/09/15 15:37
	1		US-PGPUB;	1
	1		EPO; JPO;	l
	1		DERWENT;	
			IBM_TDB	
-	32	chen.in. and chia-hsing	USPAT;	2003/09/15 15:37
			US-PGPUB;	
j	1		EPO; JPO;	
1	1		DERWENT;	
	1		IBM_TDB	